



UNITED STATES DEPARTMENT OF COMMERCE
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Washington, D.C. 20231

Date: 6-24-05

Patent No.: 6,861,614 B1

Issued : March 1, 2005

Inventor : Tanabe, et al.

Title : **S SYSTEM FOR THE FORMATION OF A SILICON THIN FILM AND A
SEMICONDUCTOR-INSULATING FILM INTERFACE**

Docket No :

Re: Request for Certificate of Correction

Consideration has been given your request for the issuance of a certificate of correction, for the above-identified patent under the provision of Rule 1.322 or R 1.323.

Respecting the alleged error, on the title page item [54], it is the practice to exclude words such as "Improvements in", "New", "A", "Novel", etc., from the printed patent. Therefore, no correction(s) is in order here under United States Codes (U.S.C.) 254 or 255 the Code of Federal Regulation (C.F.R.) R 1.322 R 1.323.

In view of the foregoing, your request is hereby denied.

Further correspondence concerning this matter should be filed and directed to Decisions and Certificates of Correction Branch. Any response must be filed within a four week period.

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